SGS-THOMSON MICROELECTRONICS

STPS640CM

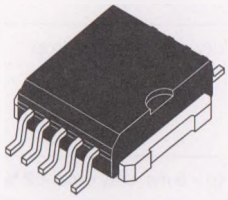
POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 3 A
V_{RRM}	45 V
V_F	0.57 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH AVALANCHE CAPABILITY
- HIGH DISSIPATION MINIATURE PACKAGE
- SURFACE MOUNT TECHNOLOGY COMPATIBLE



Power SO-10™
Plastic, non isolated SMD
with copper tab

DESCRIPTION

Dual schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in a high performance surface mount package PSO-10, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage			40	V
$I_{F(RMS)}$	RMS Forward Current	All pins connected	Per diode	11	A
$I_{F(AV)}$	Average Forward Current $\delta = 0.5$	Tc = 135°C	Per diode	3	A
			Per device	6	
I_{FSM}	Surge Non Repetitive Forward Current	tp = 10 ms Sinusoidal All pins connected	Per diode	75	A
I_{RRM}	Repetitive Peak Reverse Current	tp = 2 µs F = 1KHz	Per diode	1	A
Tstg Tj	Storage and Junction Temperature Range			- 65 to + 150	°C
dV/dt	Critical Rate of Rise of Reverse Voltage			1000	V/µs

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{TH\ (j-c)}$	Junction to Case Thermal Resistance	Per diode total	5.5 3.0	°C/W
$R_{TH\ (c)}$	Coupling Thermal Resistance		0.5	°C/W

STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage Current	Tj = 25°C	$V_R = V_{RRM}$			100	µA
		Tj = 125°C				10	mA
V_F **	Forward Voltage drop	Tj = 125°C	I_F = 6 A			0.72	V
		Tj = 125°C	I_F = 3 A			0.57	
		Tj = 25°C	I_F = 6 A			0.84	

Pulse test : * tp = 5 ms, duty cycle < 2 %
** tp = 380 µs, duty cycle < 2%

To evaluate the conduction losses use the following equation :
$P = 0.42 \times I_{F(AV)} + 0.050\ I_{F^2(RMS)}$

PIN OUT configuration in PowerSO-10 :

Anode 1 = pin 1 to 5
Anode 2 = pin 6 to 10
Cathodes = connected to base tab

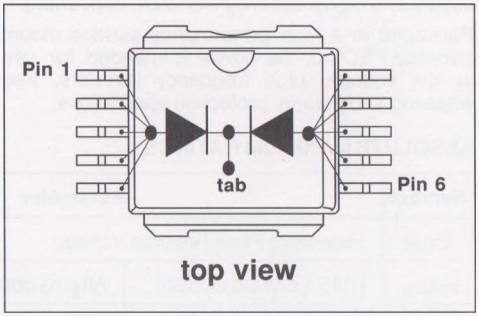

Fig. 1 : Average forward power dissipation versus average forward current. (Per diode)

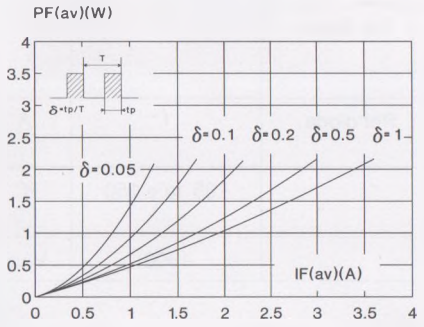

Fig. 2 : Average current versus ambient temperature.

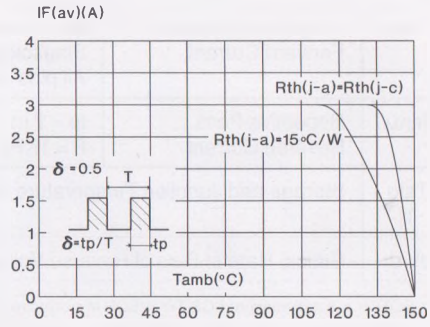

Fig. 3 : Non repetitive surge peak forward current versus overload duration.
(Maximum values) (Per diode)

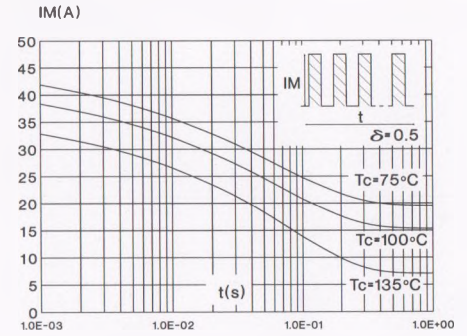

Fig. 4 : Relative variation of thermal transient impedance junction to case versus pulse duration.

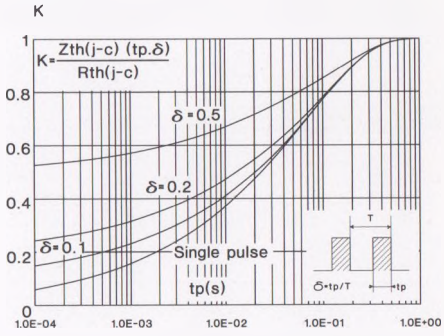

Fig. 5 : Reverse leakage current versus reverse voltage applied. (Typical values) (Per diode)

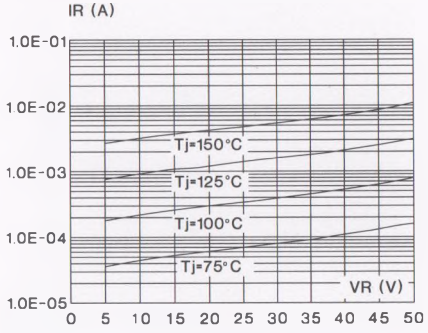

Fig. 6 : Junction capacitance versus reverse voltage applied. (Typical values) (Per diode)

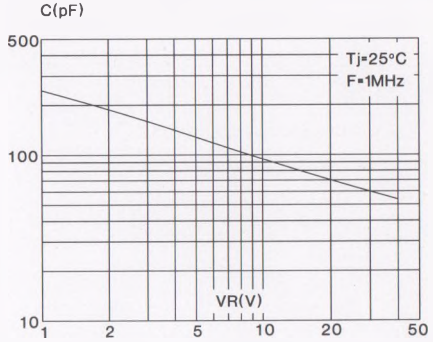

Fig. 7 : Forward voltage drop versus forward current. (Maximum values) (Per diode)